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(54) **METHOD AND SYSTEM FOR DUAL STRETCHING OF WAFERS FOR ISOLATED SEGMENTED CHIP SCALE PACKAGES**

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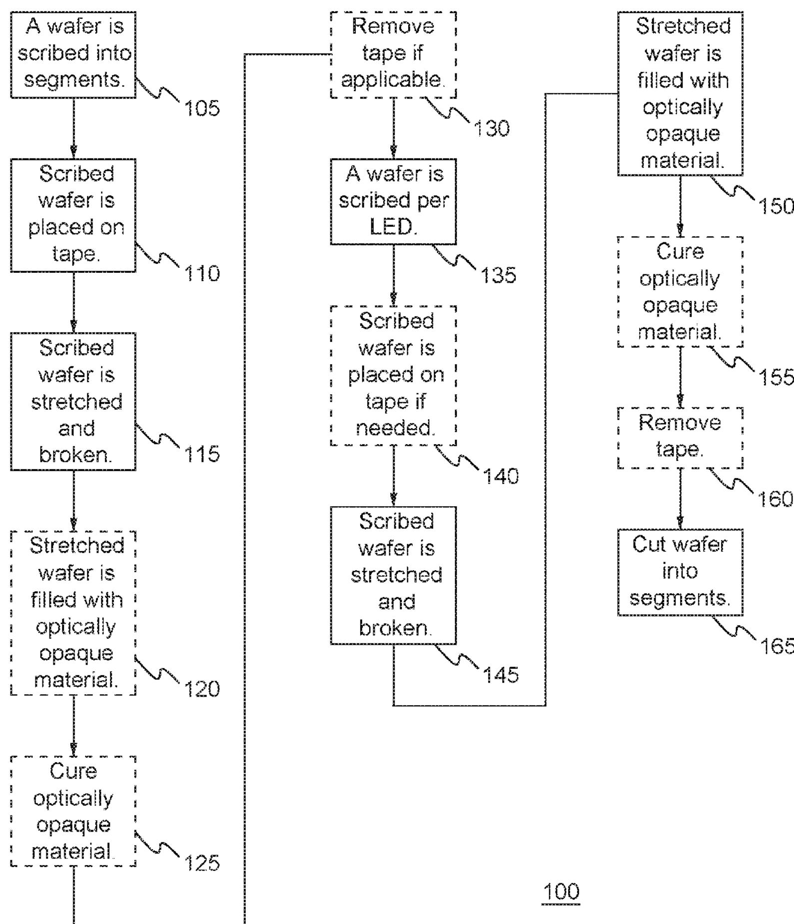
(52) **U.S. Cl.**
CPC ***H01L 21/67132*** (2013.01); *H01L 2924/01015* (2013.01); ***H01L 24/97*** (2013.01); ***H01L 24/96*** (2013.01)

(57) **ABSTRACT**

Described herein is a method and system for dual stretching of wafers to create isolated segmented chip scale packages. A wafer having an array of light-emitting diodes (LEDs) is scribed into LED segments, where each LED segment includes a predetermined number of LEDs. The scribed wafer is placed on a stretchable substrate or tape. The tape is stretched and a layer of optically material is placed in the separation gaps. The stretched wafer is scribed on a LED level. The tape is stretched and another layer of optically opaque material is placed in the separation gaps. The same or different optically opaque material can be used for the layers. The two layers of optically opaque material are formed to provide electrical connectivity between the LEDs in each LED segment. In an implementation, each segment or LED is individually addressable.



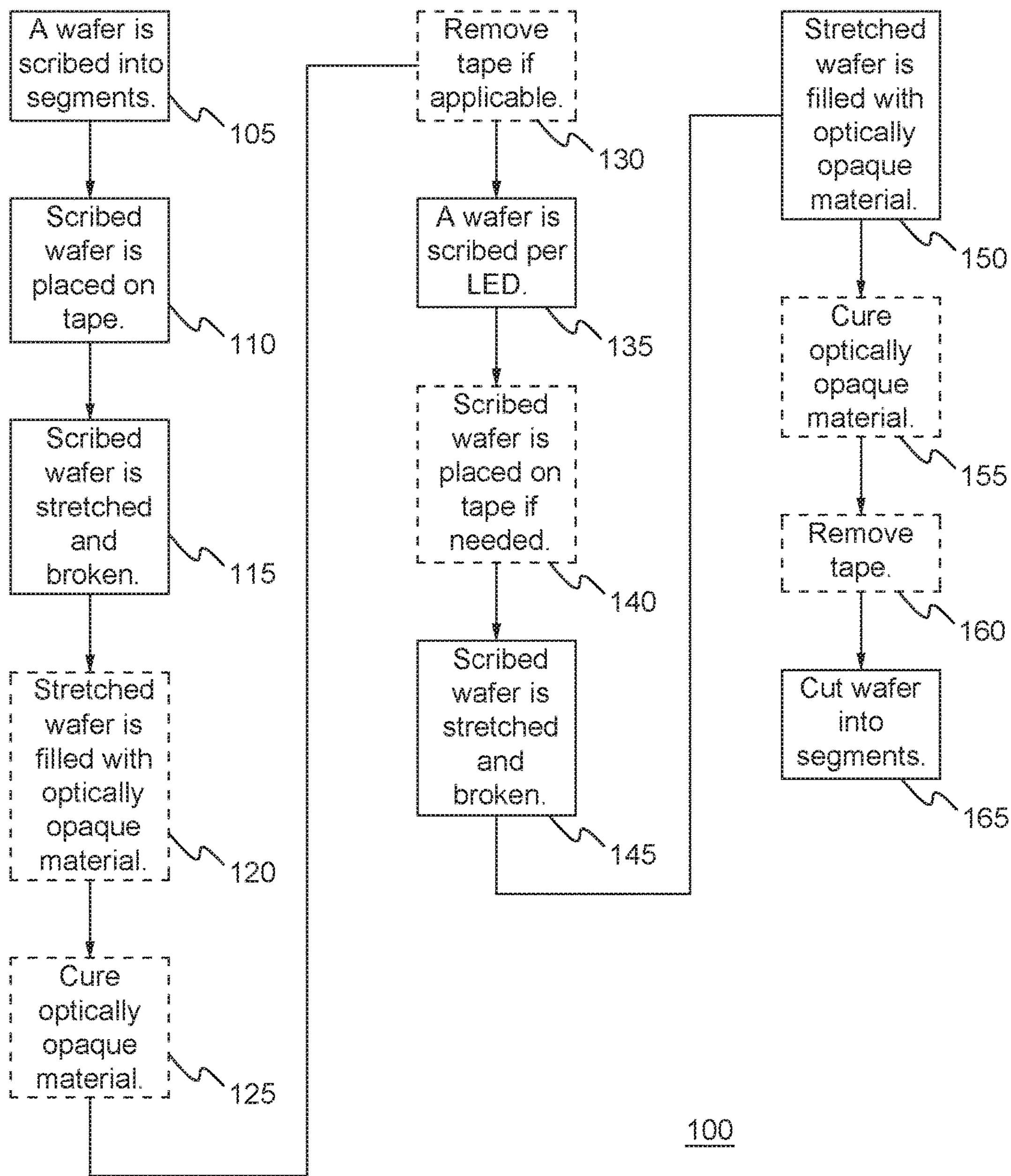


FIG. 1

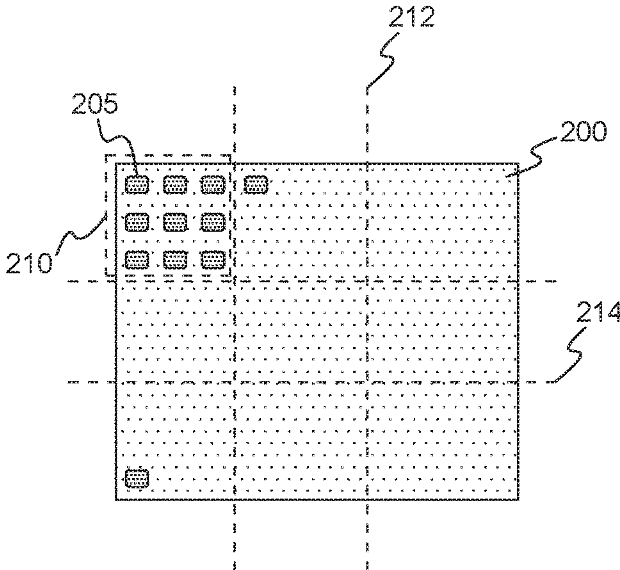


FIG. 2

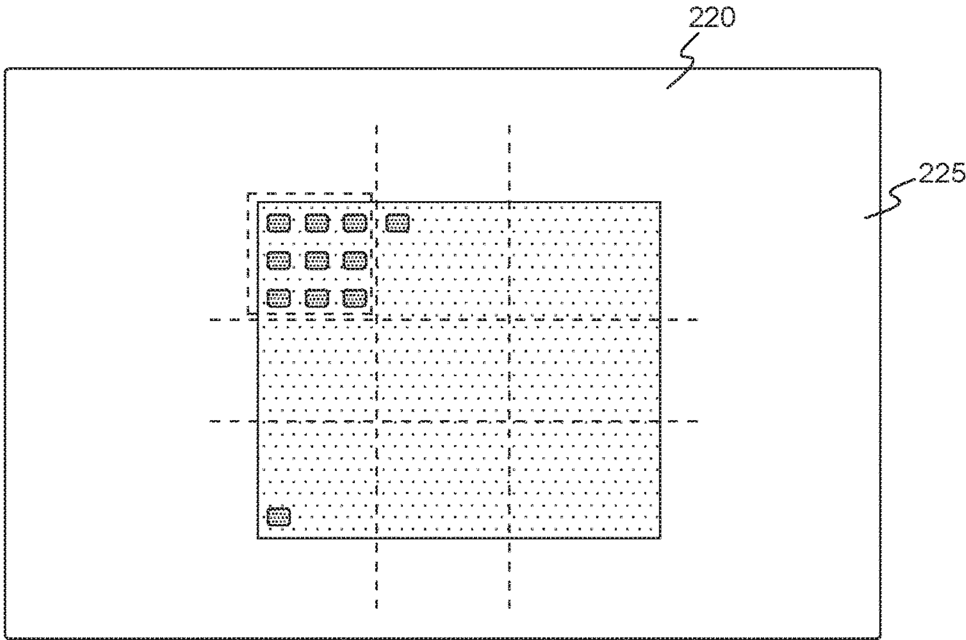


FIG. 3

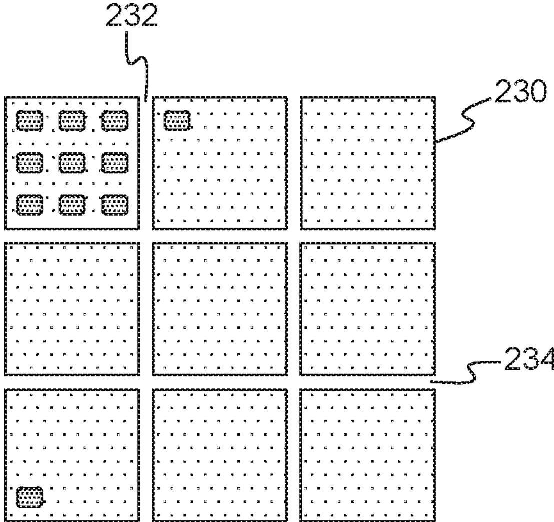


FIG. 4

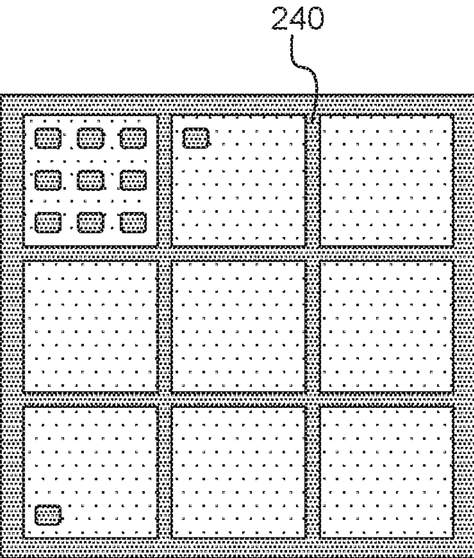


FIG. 5

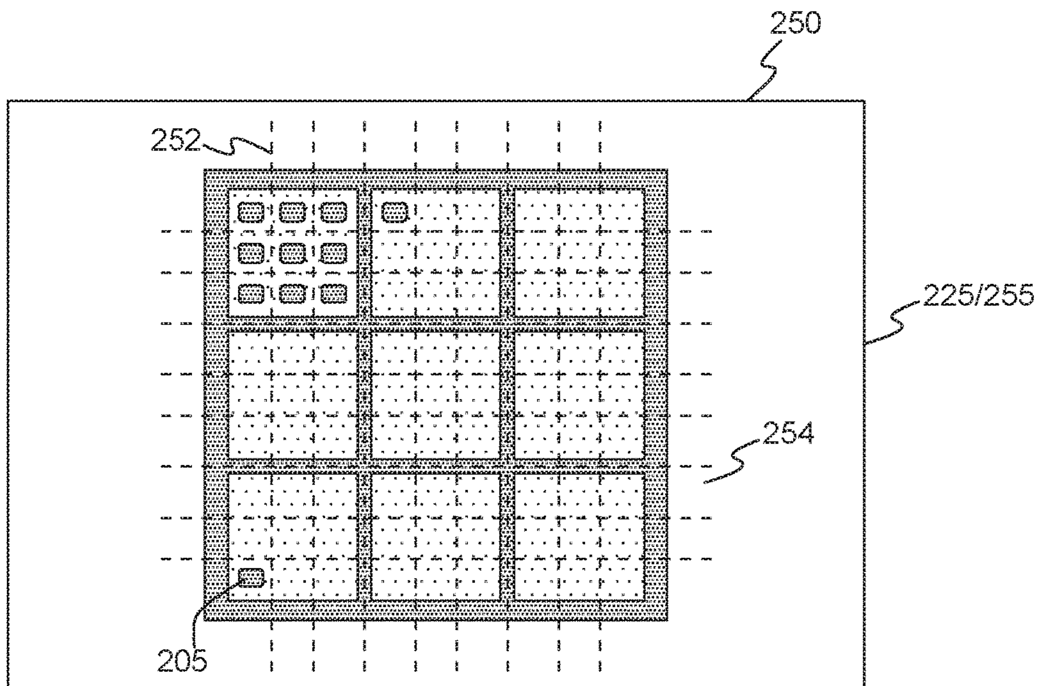


FIG. 6

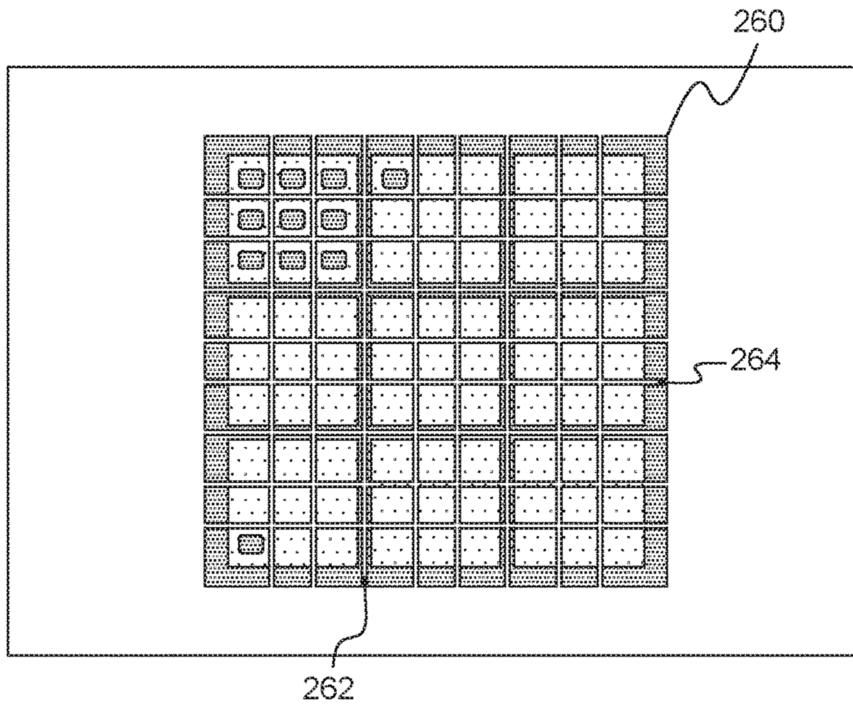


FIG. 7

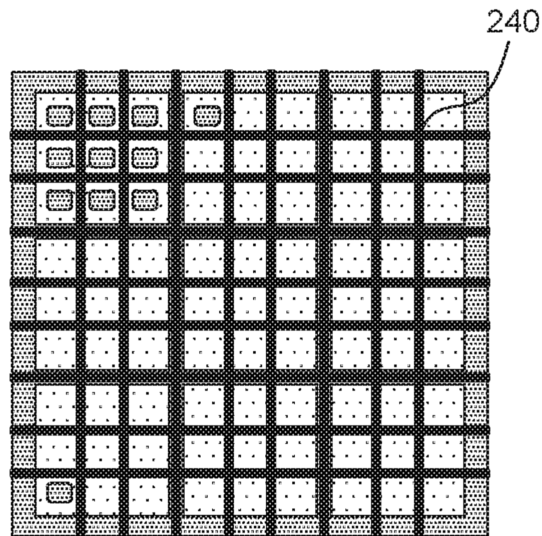


FIG. 8

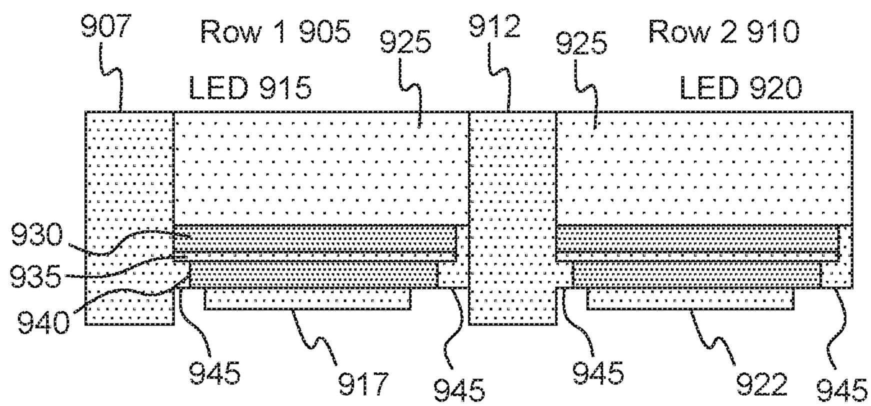


FIG. 9

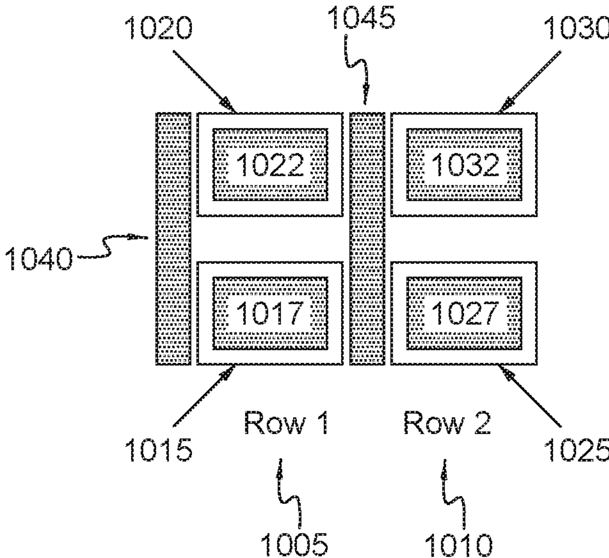


FIG. 10

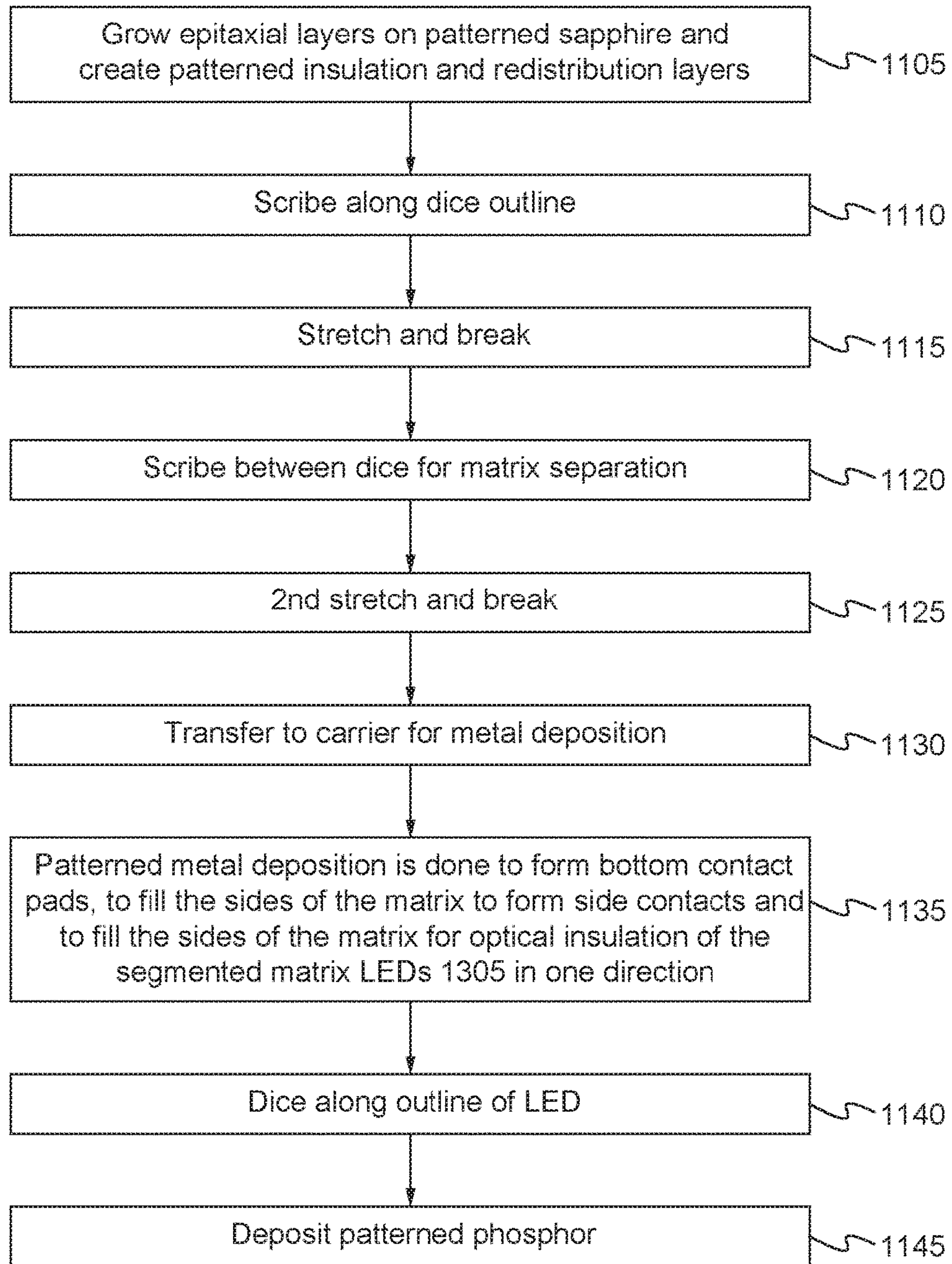


FIG. 11

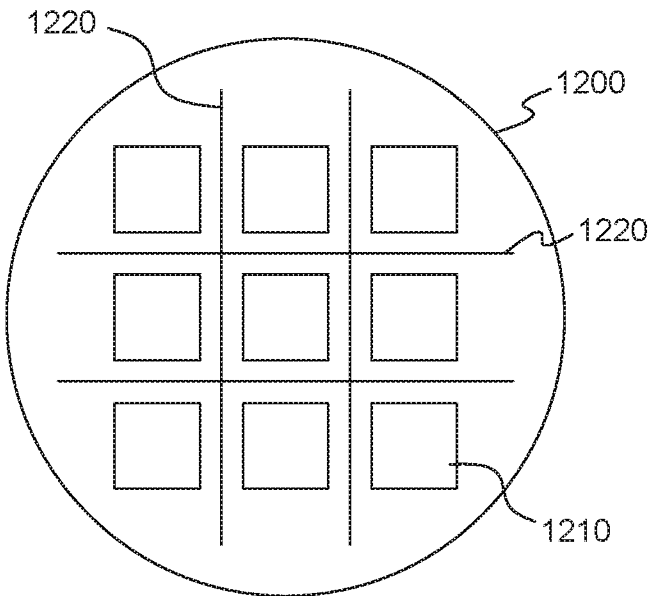


FIG. 12

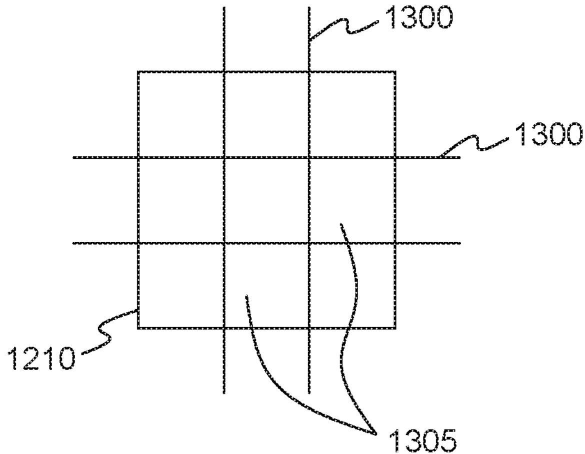


FIG. 13

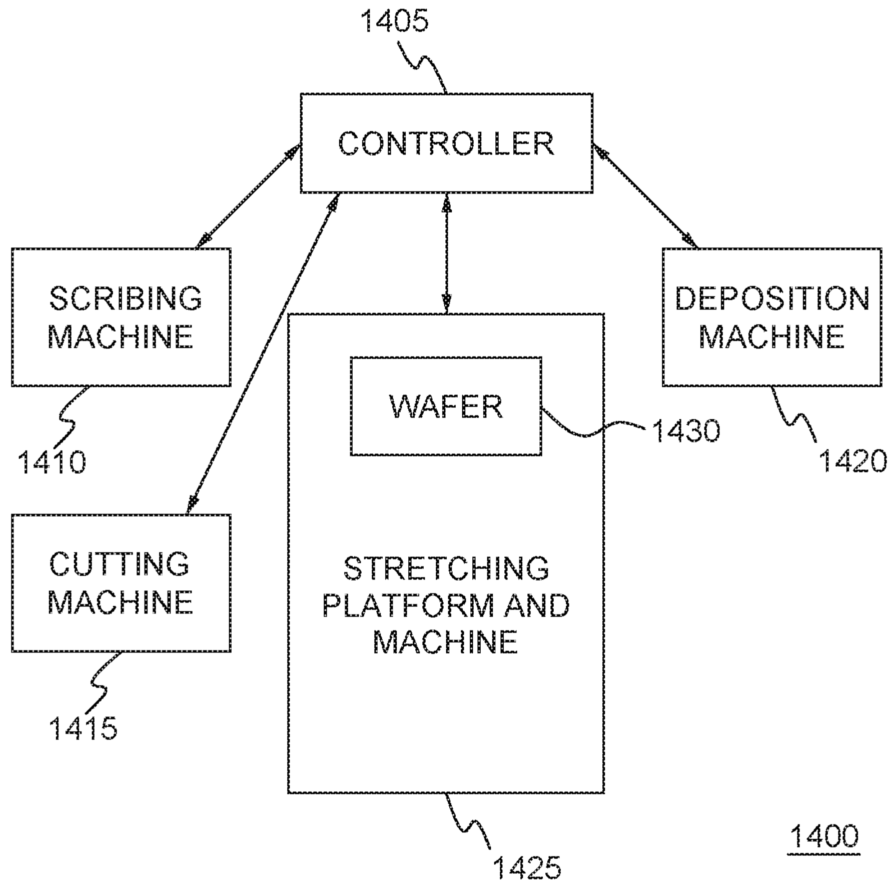


FIG. 14

METHOD AND SYSTEM FOR DUAL STRETCHING OF WAFERS FOR ISOLATED SEGMENTED CHIP SCALE PACKAGES

CROSS REFERENCE TO RELATED APPLICATION(S)

[0001] This application claims the benefit of U.S. Provisional Application Ser. No. 62/609,524 filed Dec. 22, 2017, which is incorporated by reference as if fully set forth.

FIELD OF THE INVENTION

[0002] This application is related to light-emitting diode packaging.

BACKGROUND

[0003] Segmented matrix light-emitting diodes (LEDs) can be used in camera flash or lighting applications (referred to as "adaptive flash") to illuminate a scene more homogenously. These segmented matrix LEDs devices avoid overexposure by diming the flash light on objects close by and instead use the flash light for objects that are further away. Creating a segmented matrix LED can be expensive unless wafer level processing is used.

[0004] To achieve a good contrast in the scene illumination, the optics essentially image the LED onto the scene. Any color variations of the source luminance could lead to color shading in the scene. For white LEDs, typical color variations originate from locally over-converting the light, (i.e., yellow light by e.g. locally thicker phosphor layers). For segmented LEDs, the risk is even higher. Typically, one segment could be switched on while the neighbor segment is still off. With a monolithic matrix LED, the sapphire or phosphor layer could be thought of as made from one piece or block. Unfortunately, this can lead to light guiding inside each of the blocks, i.e. the sapphire and phosphor blocks. Due to different extraction efficiencies in each of the blocks, e.g., blue light from the sapphire block and yellow from the phosphor block, white segments, (which are approximately the targeted sum of blue and yellow light), may have a yellow rim, ("over" converted light in the phosphor layer).

[0005] Scene illumination with adaptive flash or adaptive infra-red (IR) requires that the illumination sources, whether IR or visible light sources, be well separated in order to maximize contrast. Wafer level processing of light emitters is preferred for cost and reliability reasons, but widely separating the light emitters on a wafer would waste space and increase costs. Moreover, space is precious in the end products such as mobile phones. The imaging optics would also be challenged if the separation lines in the emitter were too broad. Wafer level processing that ends with closely packed but optically well separated light emitters in the same package is needed.

SUMMARY

[0006] Described herein is a method and system for dual stretching of wafers to create isolated segmented chip scale packages. A wafer having an array of light-emitting diodes (LEDs) is scribed into segments, where each segment includes a predetermined number of LEDs. The scribed wafer is placed on a stretchable substrate or tape. The tape is stretched and a layer of optically opaque, either highly reflective or absorbing, material is placed in the separation gaps. The stretched wafer is scribed on a LED level. The tape is stretched and another layer of optically opaque material is placed in the separation gaps. The two layers of optically opaque material can be chosen to also provide electrical connectivity between the LEDs in each segment. In an implementation, each segment or LED is individually addressable.

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] A more detailed understanding may be had from the following description, given by way of example in conjunction with the accompanying drawings wherein:

[0008] FIG. **1** is a flowchart of a method for dual stretching of a wafer for isolated chip scale package segments in accordance with an implementation;

[0009] FIG. **2** is an example wafer portion that is scribed in accordance with the flowchart of FIG. **1**;

[0010] FIG. **3** is an example scribed wafer portion on a tape in accordance with the flowchart of FIG. **1**;

[0011] FIG. **4** is an example wafer portion that is stretched in accordance with the flowchart of FIG. **1**;

[0012] FIG. **5** is an example wafer portion that is filled with an optically opaque material in accordance with the flowchart of FIG. **1**;

[0013] FIG. **6** is an example wafer portion that is scribed in segments in accordance with the flowchart of FIG. **1**;

[0014] FIG. **7** is an example wafer portion that is stretched in segments in accordance with the flowchart of FIG. **1**;

[0015] FIG. **8** is an example wafer portion that is filled in segments in accordance with the flowchart of FIG. **1**;

[0016] FIG. **9** is a cross-sectional view of a flip chip package in accordance with an implementation;

[0017] FIG. **10** is a top or bottom view of a flip chip package in accordance with an implementation;

[0018] FIG. **11** is another flowchart of a method for dual stretching of a wafer for isolated chip scale package segments in accordance with an implementation;

[0019] FIG. **12** is an illustrative example of scribing along LED outlines in accordance with an implementation;

[0020] FIG. **13** is an illustrative example of scribing each LED in accordance with an implementation; and

[0021] FIG. **14** is a system for implementing the flowcharts of FIG. **1** and FIG. **11** and producing the packages of FIG. **9** and FIG. **10** in accordance with an implementation.

DETAILED DESCRIPTION

[0022] It is to be understood that the figures and descriptions for a method and system for dual stretching of wafer for isolated chip scale package segments have been simplified to illustrate elements that are relevant for a clear understanding, while eliminating, for the purpose of clarity, many other elements found in typical device processing. Those of ordinary skill in the art may recognize that other elements and/or steps are desirable and/or required in implementing the present invention. However, because such elements and steps are well known in the art, and because they do not facilitate a better understanding of the present invention, a discussion of such elements and steps is not provided herein.

[0023] Described herein is a method and system for dual stretching of wafer for isolated segmented chip scale package. FIG. **1** is a flowchart of a method **100** for dual stretching of wafer for isolated segmented chip scale package in accordance with an implementation. FIG. **1**. is described in

conjunction with FIGS. **2-7**, which depicts a wafer or wafer portion, (collectively referred to as wafer herein), as it undergoes method **100**. A wafer **200** having an array of light-emitting diodes (LEDs) or light emitters **205** is scribed in segments **210** as shown in FIG. **2** (**105**). In particular, FIG. **2** illustrates vertical scribe lines **212** and horizontal scribe lines **214**. In an implementation, scribing can be implemented in one direction or both directions. LEDs **205** can include, but are not limited to, vertical-cavity surface-emitting lasers (VCSELs), and visible light emitters. LEDs **205** can be configured for any color.

[0024] A scribed wafer **220** is placed on a stretchable substrate or tape **225**, (collectively referred to as tape herein), as shown in FIG. **3** (**110**). In an implementation, wafer **200** can be placed on tape **225** and then scribed. Tape **225** is stretched to separate along vertical scribe lines **212** and horizontal scribe lines **214**, resulting in a separated wafer **230** with vertical separation gaps **232** and horizontal separation gaps **234** as shown in FIG. **4** (**115**). An optically opaque material **240** is deposited in vertical separation gaps **222** and horizontal separation gaps **224** as shown in FIG. **5** (**120**). Optically opaque material **240** can be, but is not limited to, Titanium Oxide embedded in silicone, dielectric layers forming a distributed Bragg reflector (DBR), metal and other similar materials. In an implementation, optically opaque material **240** is generally of a particle size that permits flow into vertical separation gaps **232** and horizontal separation gaps **234** via, for example, capillary forces. Optically opaque material **240** in then allowed to harden or cure, as appropriate (**125**). In an implementation, metal deposition techniques including, but not limited to, sputtering or anisotropic grow processes with lift-off techniques or 3D printing electrodeposition can be used when the optically opaque material **240** is metal. In an implementation where only one direction is scribed, the above process (steps **100-125**) can be repeated for the other direction. In an implementation, tape **225** is re-used for a second stretching process. In an implementation, tape **225** can be removed (**130**).

[0025] A first stretched wafer **250** is then scribed on a LED **205** level as shown in FIG. **6** (**135**). In particular, FIG. **6** illustrates vertical scribe lines **252** and horizontal scribe lines **254**. In an implementation where tape **225** has been removed, first stretched wafer **250** is placed on a second tape **255** (**140**). Tape **225** or **255** is stretched to separate along vertical scribe lines **252** and horizontal scribe lines **254**, resulting in a second separated wafer **260** with vertical separation gaps **262** and horizontal separation gaps **264** as shown in FIG. **7** (**145**). Optically opaque material **240** is deposited in vertical separation gaps **262** and horizontal separation gaps **264** as shown in FIG. **8** (**150**). Optically opaque material **240** in then allowed to harden or cure, as appropriate (**155**). In an implementation where only one direction is scribed, the above process (steps **135-155**) can be repeated for the other direction. In an implementation, tape **225/255** is removed (**160**). Each of the segments **210** is then cut using known techniques (**165**).

[0026] In an implementation, different materials can be used for optically opaque material **240** for filling separation gaps. In an implementation, multiple layers of optically opaque material **240** can be deposited as described herein below.

[0027] In an implementation, where optically opaque material **240** is a metal, the layers of optically opaque material are formed and configured to provide electrical connectivity between the LEDs in each segment. In an implementation, a non-conductive or insulation layer or film can be deposited to provide electrical separation between the metal layers. In an implementation, photoresist masks can be used to implement contacts to the LEDs. Other techniques known to one of skill in the art can be used to effectuate electrical connections to the LEDs. In an implementation, use of large bottom pads on the LEDs and side metal contacts can increase thermal performance. In an implementation, the configuration of the layers allows each LED or group of LEDs to be individually addressable.

[0028] FIGS. **9** and **10** are illustrative cross-sectional and top/bottom views of the isolated segmented chip packages made in accordance with the flowcharts of FIG. **1** or FIG. **11** as appropriate.

[0029] FIG. **9** is a cross-sectional view of a flip chip package **900** in accordance with certain implementations. Flip chip package **900** includes at least two rows, row **1 905** and row **2 910**. Row **1 905** includes LED **915** and row **2 910** includes LED **920**. Each LED **915** and **920** includes a patterned sapphire substrate **925** on which is grown a n-type Gallium Nitride (GaN) layer **930**, an active layer **935** and a p-type GaN layer **940**. Active layer **935** can be configured to include a light emitting diode. LEDs **915** and **920** each have a bottom/top contact pad **917** and **922**, respectively, for contacting with p-type GaN layer **940**, for example. Row **1 905** and row **2 910** each have a side contact pad **907** and **912**, respectively, i.e., optically opaque material **240**, for contacting to n-type GaN layer **930**. Insulation layers **945** are deposited to provide electrical separation to enable addressability.

[0030] FIG. **10** is a bottom/top view of a flip chip package **1000**. Flip chip package **1000** includes at least two rows, row **1 1005** and row **2 1010**. Row **1 1005** includes multiple LEDs, for example LEDs **1015** and **1020**, and row **2 1010** includes LEDs **1025** and **1030**. Each LED has bottom/top contact pad for contacting to an n-type GaN layer or a p-type GaN layer in the LED as shown in FIG. **9**. For example, LEDs **1015**, **1020**, **1025** and **1030** each have a bottom/top contact pad **1017**, **1022**, **1027** and **1032**, respectively. Each row has a side contact pad, i.e., optically opaque material **240**, for contacting to a remaining one of n-type GaN layer or p-type GaN layer in the LED. For example, in row **1 1005**, side contact pad **1040** contacts LEDs **1015** and **1020** and side contact pad **1045** contacts LEDs **1025** and **1030**.

[0031] FIG. **11** is another flowchart of a method **1100** for dual stretching of a wafer for isolated chip scale package segments in accordance with an implementation. An illustrative wafer **1200** is shown in FIG. **12**. The wafer **1200** is for example a patterned sapphire substrate. Epitaxial layers are grown on a patterned sapphire substrate and patterned insulation and redistribution layers are created (**1105**). The wafer has, for example, LEDs **1210**. The wafer **1200** is placed on a tape and scribed along an outline **1220** of dice or LEDs **1210** (**1110**). The wafer **1200** is stretched and broken by stretching the tape (**1115**). The once broken wafer **1200** is scribed a 2nd time along interior scribe lines **1300** (as shown in FIG. **13**) for each of the LEDs **1210** for matrix separation (i.e. to create segmented matrix LEDs **1305** from each of the LEDs **1210**) (**1120**). The tape is stretched and broken again (**1125**). The separation lanes (formed along scribe lines **1220**) for the LEDs **1210** (which are now twice stretched) will be bigger than the separation lanes formed

along interior scribe lines **1300** of the LEDs **1210**. This makes it easier to separate the LEDs **1210** and leaves smaller gaps only between the segmented matrix LEDs **1305**.

[0032] The now segmented wafer **1200** on the twice stretched tape is transferred to a sputter compliant carrier, for example a glass substrate for metal deposition, e.g. aluminum (**1130**). Patterned metal deposition is done to form bottom contact pads, to fill the sides of the matrix to form side contacts in one direction and to fill the sides of the matrix for optical insulation of the segmented matrix LEDs **1305** in another direction (**1135**). For example, side contacts are formed in a vertical or horizontal direction. The remaining direction, horizontal or vertical, is filled with optical insulation material. The metal filling is done to the depth necessary to ensure side electrical contact with n-type GaN layer **930**, for example. After sputtering, targeted patterned design can be done by an etching step to remove excess or unwanted metal. The insulation material **945**, for example, is selected or coated with, for example, silicon nitride or silicon oxide, to create an etching stop. Optical insulation is finalized by filling horizontal lanes, (gap between **1020** and **1015** as well as **1030** and **1025** in FIG. **10**), for example, and by filling the partially filled vertical lanes (**1040** and **1045** in FIG. **10**), for example, as needed. The wafer **1210** is diced along the outlines **1220** of the LEDs **1210** (**1140**). Patterned phosphor deposition is done on each of the diced LEDs **1210** (**1150**).

[0033] In an implementation, filling can be done after the first stretch and after the 2nd stretch. This allows the use of a different material for the 2 gaps. In an implementation, gaps are filled only after the 2 stretches.

[0034] FIG. **14** is a system **1400** for implementing the flowchart of FIG. **1** in accordance with an implementation. System **1400** can include a controller **1405** communicatively coupled or connected to, (collectively connected to herein), a scribing machine **1410**, a cutting machine **1415**, a deposition machine **1420**, and a stretching platform and machine **1425**. Scribing machine **1410** is used to scribe a wafer **1430** as described herein. After scribing the wafer **1300**, the scribed wafer **1300** is placed on stretching platform and machine **1425** for stretching. A deposition machine **1420** is used to deposit the optically opaque material after the first stretching, after the seconding stretching or combinations thereof. Upon completion of the stretching to create segments as in FIG. **1** or segmented matrix LEDs as in FIG. **11** and hardening of the optically opaque material, cutting machine **1415** is used to cut or dice the wafer **1300** into LED packages for use in electronic packages. The machines described herein are illustrative and other similar machines can be used.

[0035] The embodiments described herein may be used for any suitable LED and/or light emitting device. Embodiments of the invention are not limited to the particular structures illustrated, such as, for example, the wafers of FIGS. **2-7** and packages of FIGS. **9-10** and **12-13**. The principles described herein may be applicable to light emitting devices made from a variety of materials systems such as other III-V materials, III-phosphide, III-arsenide, II-VI materials, ZnO, or Si-based materials.

[0036] The non-limiting methods described herein for dual stretching of wafer for isolated chip scale package segments may be modified for a variety of applications and uses while remaining within the spirit and scope of the claims. The implementations and variations described herein, and/or shown in the drawings, are presented by way of example only and are not limiting as to the scope and spirit. The descriptions herein may be applicable to all implementations of the method for dual stretching of wafer for isolated chip scale package segments although it may be described with respect to a particular implementation.

[0037] As described herein, the methods described herein are not limited to any particular element(s) that perform(s) any particular function(s) and some steps of the methods presented need not necessarily occur in the order shown. For example, in some cases two or more method steps may occur in a different order or simultaneously. In addition, some steps of the described methods may be optional (even if not explicitly stated to be optional) and, therefore, may be omitted. These and other variations of the methods disclosed herein will be readily apparent, especially in view of the description of the method for dual stretching of wafer for isolated chip scale package segments as described herein, and are considered to be within the full scope of the invention.

[0038] Some features of some implementations may be omitted or implemented with other implementations. The device elements and method elements described herein may be interchangeable and used in or omitted from any of the examples or implementations described herein.

[0039] Although features and elements are described above in particular combinations, each feature or element can be used alone without the other features and elements or in various combinations with or without other features and elements.

What is claimed is:

1. A method for dual stretching of a wafer, the method comprising:
- scribing a wafer along at least one segment line, each segment having a predetermined number of light emitters;
- stretching first tape carrying the wafer;
- scribing the wafer along each at least one light emitter line;
- stretching second tape carrying the wafer; and
- filling gaps created by the stretching with optically opaque material.

2. The method of claim **1**, the method further comprising:
- cutting the wafer into light emitter segments.

3. The method of claim **1**, wherein the wafer is scribed along two segment lines.

4. The method of claim **3**, wherein the wafer is scribed along two light emitter lines.

5. The method of claim **1**, the method further comprising:
- filling gaps created by a first stretching with the optically opaque material.

6. The method of claim **1**, wherein the optically opaque material is a metal.

7. The method of claim **1**, the method further comprising:
- depositing insulation layers to provide electrical separation between metal layers.

8. The method of claim **6**, wherein the metal provides electrical connectivity between the segments.

9. The method of claim **6**, wherein the metal provides electrical connectivity between the light emitters.

10. The method of claim **5**, wherein the first tape and the second tape are same.

11. A method for dual stretching of a wafer, the method comprising:

scribing a patterned substrate along light emitter outlines between light emitters on the wafer;

stretching tape carrying the wafer to break along the light emitter outlines;

scribing the patterned substrate along interior lines of each light emitter on the wafer;

stretching the tape carrying the wafer to break along the interior lines;

filling gaps in one direction created by the stretching with metal to form side contacts; and

dicing the patterned substrate along the light emitter outlines to form light emitter segments.

12. The method of claim **11**, the method further comprising:

depositing an insulation layer in the one direction to provide optical insulation.

13. The method of claim **12**, wherein a depth of the insulation layer ensures electrical connectivity of the side contacts.

14. The method of claim **13**, the method further comprising:

depositing the insulation layer in other gaps created by the stretching to provide optical insulation.

15. The method of claim **11**, the method further comprising:

forming one of top or bottom contact pads by patterned metal deposition.

16. The method of claim **11**, the method further comprising:

growing epitaxial layers on the patterned substrate.

17. The method of claim **11**, the method further comprising:

depositing patterned phosphor on each diced light emitter segment.

18. The method of claim **11**, the method further comprising:

transferring second stretched tape to deposition compliant carrier.

* * * * *